

Fig. 1

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ZnO thickness ~ 500 nm/Si

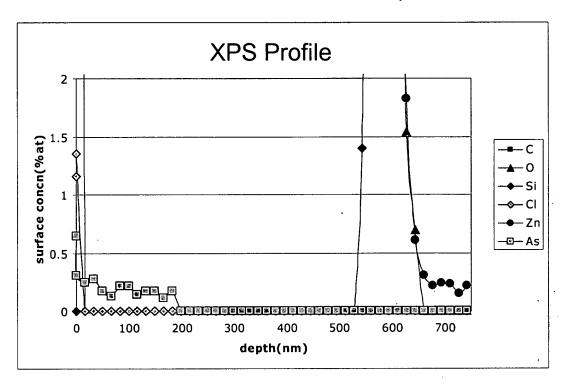


Fig. 2

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P-type ZnO: Photoluminescent Comparisons

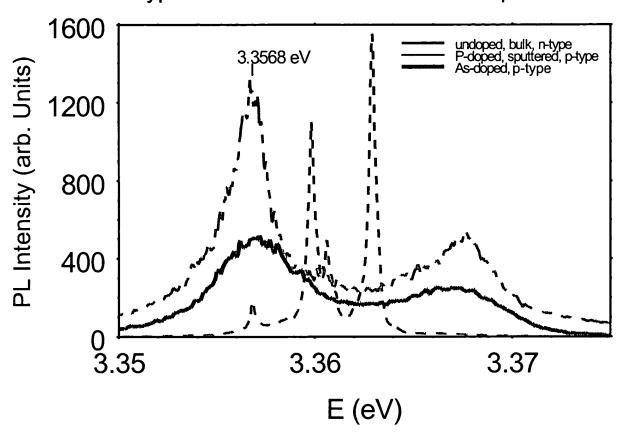


Fig. 3

DUCKET NO., 3330.2.

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Resistance & Mobility of As doped ZnO

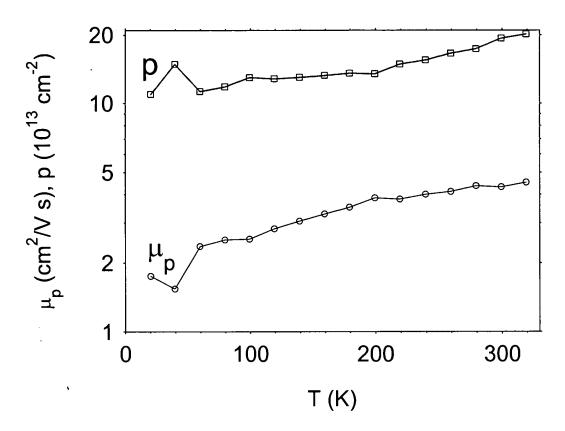


Fig. 4

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SIMS Data Showing Concentration vs. Depth

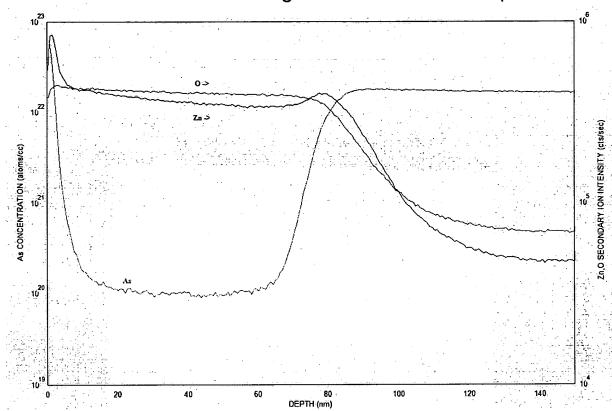


Fig. 5

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Polycrystalline Zinc Oxide XRD Pattern

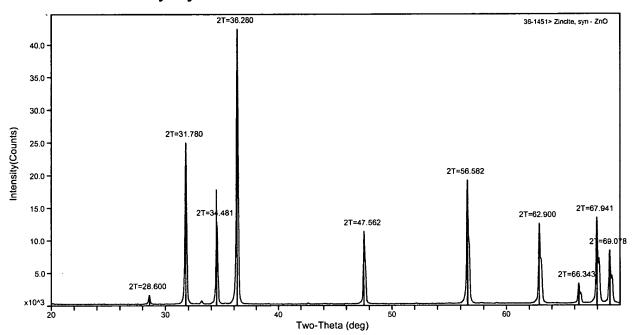


Fig. 6

Title: GROUP II-VI SEMICONDUCTOR DEVICES Inventors: Robert H. Burgener, II et al.

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Zinc Oxide XRD Pattern Showing Single Crystal (002) Plane

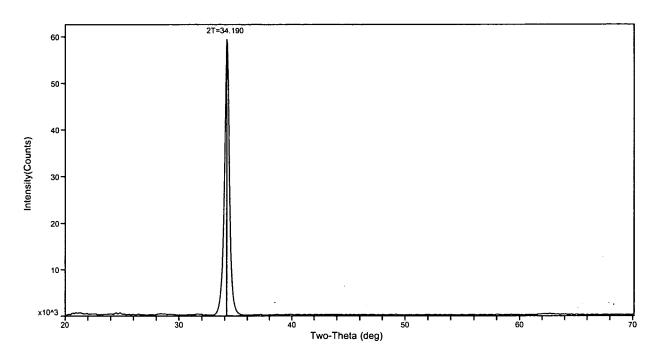


Fig. 7

Title: GROUP II-VI SEMICONDUCTOR DEVICES Inventors: Robert H. Burgener, II et al.

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8/16 Antimony Concentration In Zinc Oxide

Atoms/cm³ verses Depth Into The Surface

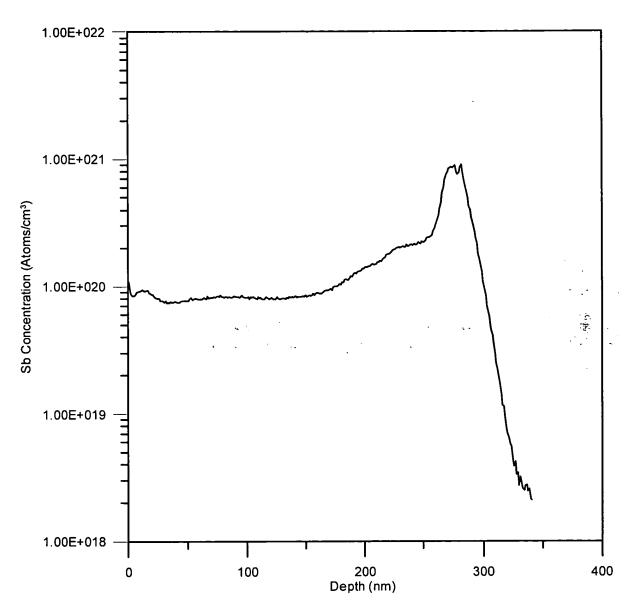


Fig. 8

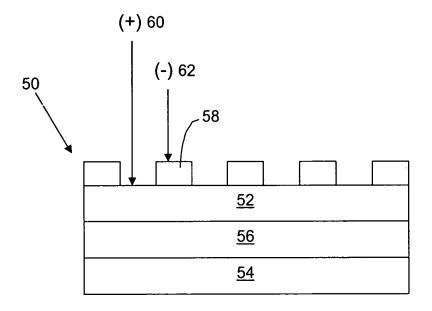


Fig. 9

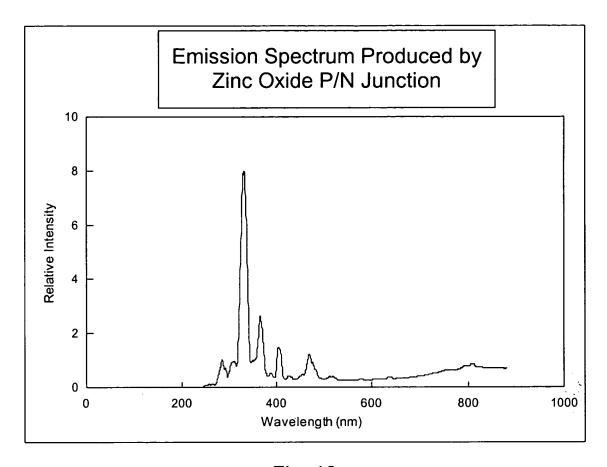


Fig. 10

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Current - Voltage Plot of a Zinc Oxide P/N Junction

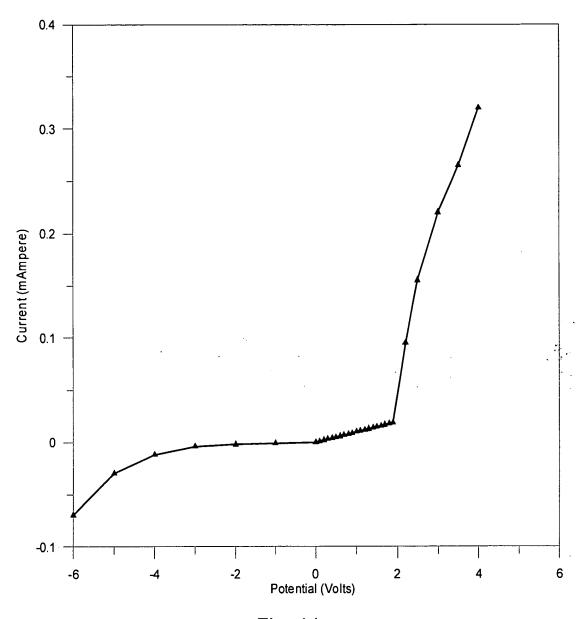


Fig. 11

Title: GROUP II-VI SEMICONDUCTOR DEVICES

Inventors: Robert H. Burgener, II et al. Docket No.: 3398.2.10

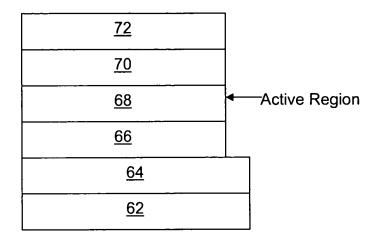


Fig. 12

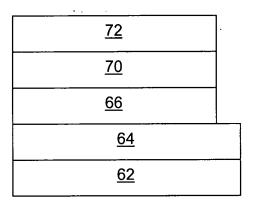
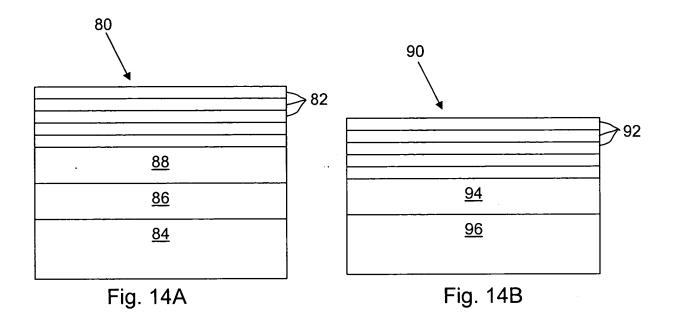


Fig. 13



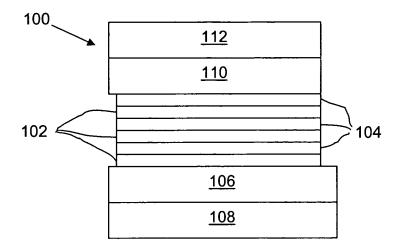


Fig. 15A

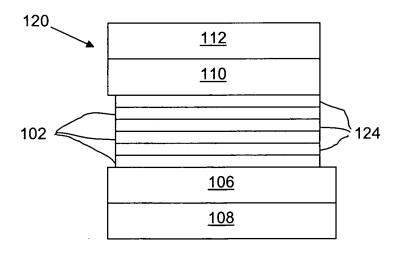


Fig. 15B

Title: GROUP II-VI SEMICONDUCTOR DEVICES Inventors: Robert H. Burgener, II et al.

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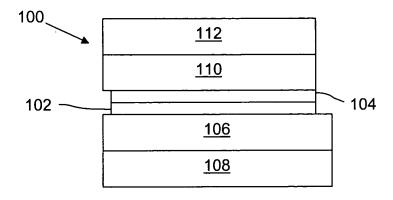


Fig. 16A

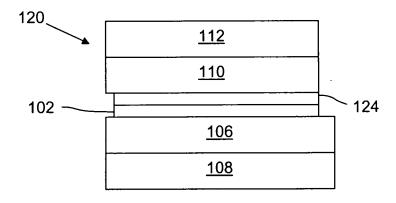
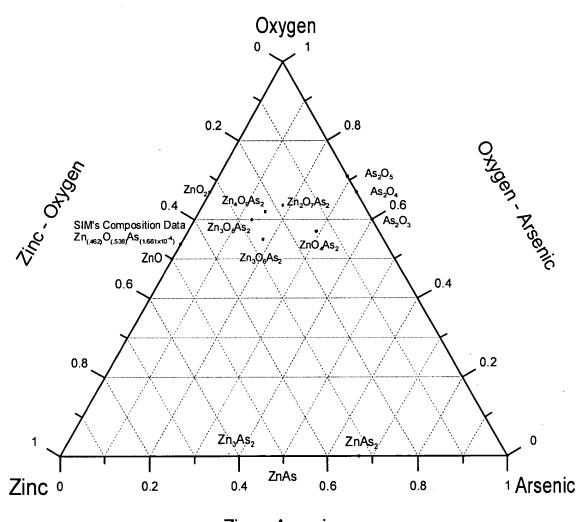


Fig. 16B

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Zinc - Oxygen - Arsenic Ternary Diagram



Zinc - Arsenic

Fig. 17